Nicolas Grandjean

List of Publications by Year in Descending Order

533 papers	15,450 citations	62 h-index	98 g-index
566 ext. papers	16,633 ext. citations	3 avg, IF	6.19 L-index

#	Paper	IF	Citations
533	Near ultraviolet photonic integrated lasers based on silicon nitride. *APL Photonics*, **2022**, 7, 046108	5.2	1
532	Single photon emission and recombination dynamics in self-assembled GaN/AlN quantum dots.. *Light: Science and Applications*, **2022**, 11, 114	16.7	4
531	Defect incorporation in In-containing layers and quantum wells: experimental analysis via deep level profiling and optical spectroscopy. *Journal Physics D: Applied Physics*, **2021**, 54, 025108	3	6
530	High conductivity InAlN/GaN multi-channel two-dimensional electron gases. *Semiconductor Science and Technology*, **2021**, 36, 055020	1.8	3
529	Imaging Nonradiative Point Defects Buried in Quantum Wells Using Cathodoluminescence. *Nano Letters*, **2021**, 21, 5217-5224	11.5	5
528	Ultrafast-nonlinear ultraviolet pulse modulation in an AlInGaN polariton waveguide operating up to room temperature. *Nature Communications*, **2021**, 12, 3504	17.4	3
527	Dark-level trapping, lateral confinement, and built-in electric field contributions to the carrier dynamics in c-plane GaN/AlN quantum dots emitting in the UV range. *Journal of Applied Physics*, **2021**, 129, 054301	2.5	3
526	Smooth GaN membranes by polarization-assisted electrochemical etching. *Applied Physics Letters*, **2021**, 118, 062107	3.4	3
525	GaN buffer growth temperature and efficiency of InGaN/GaN quantum wells: The critical role of nitrogen vacancies at the GaN surface. *Applied Physics Letters*, **2021**, 118, 111102	3.4	7
524	Modeling the electrical characteristics of InGaN/GaN LED structures based on experimentally-measured defect characteristics. *Journal Physics D: Applied Physics*, **2021**, 54, 425105	3	2
523	Effects of quantum-well indium content on deep defects and reliability of InGaN/GaN light-emitting diodes with under layer. *Journal Physics D: Applied Physics*, **2021**, 54, 505108	3	0
522	Toward Bright and Pure Single Photon Emitters at 300 K Based on GaN Quantum Dots on Silicon. *ACS Photonics*, **2020**, 7, 1515-1522	6.3	24
521	Impact of defects on Auger recombination in c-plane InGaN/GaN single quantum well in the efficiency droop regime. *Applied Physics Letters*, **2020**, 116, 222106	3.4	6
520	Deep traps in InGaN/GaN single quantum well structures grown with and without InGaN underlayers. *Journal of Alloys and Compounds*, **2020**, 845, 156269	5.7	2
519	III-nitride photonic cavities. *Nanophotonics*, **2020**, 9, 569-598	6.3	13
518	Doubly resonant second-harmonic generation of a vortex beam from a bound state in the continuum. *Optica*, **2020**, 7, 1126	8.6	17
517	Broadened Bandwidth Amplified Spontaneous Emission from Blue GaN-Based Short-Cavity Superluminescent Light-Emitting Diodes. *ECS Journal of Solid State Science and Technology*, **2020**, 9, 015019	2	5

516	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. *Journal Physics D: Applied Physics*, **2020**, 53, 445111	3	3
515	Interplay of intrinsic and extrinsic states in pinning and passivation of m-plane facets of GaN n-p-n junctions. *Journal of Applied Physics*, **2020**, 128, 185701	2.5	
514	Effects of InAlN underlayer on deep traps detected in near-UV InGaN/GaN single quantum well light-emitting diodes. *Journal of Applied Physics*, **2019**, 126, 125708	2.5	14
513	InAlN underlayer for near ultraviolet InGaN based light emitting diodes. *Applied Physics Express*, **2019**, 12, 034002	2.4	23
512	Density control of GaN quantum dots on AlN single crystal. *Applied Physics Letters*, **2019**, 114, 082101	3.4	14
511	Short cavity InGaN-based laser diodes with cavity length below 300 □m. *Semiconductor Science and Technology*, **2019**, 34, 085005	1.8	5
510	Low-temperature growth of n ++-GaN by metalorganic chemical vapor deposition to achieve low-resistivity tunnel junctions on blue light emitting diodes. *Semiconductor Science and Technology* , **2019**, 34, 015002	1.8	7
509	Impact of Mode-Hopping Noise on InGaN Edge Emitting Laser Relative Intensity Noise Properties. *IEEE Journal of Quantum Electronics*, **2018**, 54, 1-7	2	5
508	A quantum optical study of thresholdless lasing features in high-□nitride nanobeam cavities. *Nature Communications*, **2018**, 9, 564	17.4	38
507	Optical absorption edge broadening in thick InGaN layers: Random alloy atomic disorder and growth mode induced fluctuations. *Applied Physics Letters*, **2018**, 112, 032106	3.4	21
506	Impact of surface morphology on the properties of light emission in InGaN epilayers. *Applied Physics Express*, **2018**, 11, 051004	2.4	5
505	Optical absorption and oxygen passivation of surface states in III-nitride photonic devices. *Journal of Applied Physics*, **2018**, 123, 113103	2.5	16
504	Near-UV narrow bandwidth optical gain in lattice-matched III□itride waveguides. *Japanese Journal of Applied Physics*, **2018**, 57, 090305	1.4	1
503	Excited states of neutral donor bound excitons in GaN. *Journal of Applied Physics*, **2018**, 123, 215702	2.5	3
502	In distribution in InGaN quantum wells: influence of phase separation, In segregation and In desorption **2018**, 285-288		
501	GaN surface as the source of non-radiative defects in InGaN/GaN quantum wells. *Applied Physics Letters*, **2018**, 113, 111106	3.4	65
500	Alloy disorder limited mobility of InGaN two-dimensional electron gas. *Applied Physics Letters*, **2018** , 112, 262101	3.4	16
499	Composition Metrology of Ternary Semiconductor Alloys Analyzed by Atom Probe Tomography. *Journal of Physical Chemistry C*, **2018**, 122, 16704-16714	3.8	16

498	Fermi-level pinning and intrinsic surface states of Al1−xInxN(101̄0) surfaces. *Applied Physics Letters*, **2017**, 110, 022104	3.4	4
497	Thin-Wall GaN/InAlN Multiple Quantum Well Tubes. *Nano Letters*, **2017**, 17, 3347-3355	11.5	9
496	Multilayer porous structures on GaN for the fabrication of Bragg reflectors **2017**,		3
495	Efficient continuous-wave nonlinear frequency conversion in high-Q gallium nitride photonic crystal cavities on silicon. *APL Photonics*, **2017**, 2, 031301	5.2	27
494	Enhancement of Auger recombination induced by carrier localization in InGaN/GaN quantum wells. *Physical Review B*, **2017**, 95,	3.3	35
493	Propagating Polaritons in III-Nitride Slab Waveguides. *Physical Review Applied*, **2017**, 7,	4.3	19
492	Multilayer porous structures of HVPE and MOCVD grown GaN for photonic applications. *Superlattices and Microstructures*, **2017**, 102, 221-234	2.8	14
491	Quantification of scattering loss of III-nitride photonic crystal cavities in the blue spectral range. *Physical Review B*, **2017**, 95,	3.3	9
490	AlN grown on Si(1 1 1) by ammonia-molecular beam epitaxy in the 900–1200 °C temperature range. *Journal of Crystal Growth*, **2017**, 476, 58-63	1.6	31
489	Determining the nature of excitonic dephasing in high-quality GaN/AlGaN quantum wells through time-resolved and spectrally resolved four-wave mixing spectroscopy. *Physical Review B*, **2017**, 96,	3.3	6
488	Critical thickness of GaN on AlN: impact of growth temperature and dislocation density. *Semiconductor Science and Technology*, **2017**, 32, 075010	1.8	23
487	Burying non-radiative defects in InGaN underlayer to increase InGaN/GaN quantum well efficiency. *Applied Physics Letters*, **2017**, 111, 262101	3.4	71
486	Light-emitting diode technology and applications: introduction. *Photonics Research*, **2017**, 5, LED1	6	3
485	Critical impact of Ehrlich–Schwöbel barrier on GaN surface morphology during homoepitaxial growth. *Journal of Crystal Growth*, **2016**, 433, 36-42	1.6	45
484	Statistical nanoscale study of localised radiative transitions in GaN/AlGaN quantum wells and AlGaN epitaxial layers. *Semiconductor Science and Technology*, **2016**, 31, 095009	1.8	18
483	Room-Temperature Transport of Indirect Excitons in (Al,Ga)N/GaN Quantum Wells. *Physical Review Applied*, **2016**, 6,	4.3	16
482	Carrier-density-dependent recombination dynamics of excitons and electron-hole plasma in m-plane InGaN/GaN quantum wells. *Physical Review B*, **2016**, 94,	3.3	34
481	Technology of integrated self-aligned E/D-mode n++GaN/InAlN/AlN/GaN MOS HEMTs for mixed-signal electronics. *Semiconductor Science and Technology*, **2016**, 31, 065011	1.8	9

480	GaN-based superluminescent diodes with long lifetime **2016**,		6
479	TEM study of defect reduction in the growth of semipolar GaN grown on patterned substrates **2016**, 590-591		
478	W -Band MMIC Amplifiers Based on AlInN/GaN HEMTs Grown on Silicon. *IEEE Electron Device Letters*, **2016**, 37, 1025-1028	4.4	10
477	Selective heteroepitaxy on deeply grooved substrate: A route to low cost semipolar GaN platforms of bulk quality. *Applied Physics Letters*, **2016**, 109, 082101	3.4	7
476	GaN superluminescent diodes and their applications **2016**,		1
475	High p-type GaN for advanced optoelectronic devices **2016**,		1
474	Far-field coupling in nanobeam photonic crystal cavities. *Applied Physics Letters*, **2016**, 108, 201104	3.4	4
473	Photocapacitance spectroscopy of InAlN nearly lattice-matched to GaN. *Applied Physics Letters*, **2016**, 109, 152102	3.4	4
472	Assessing the Composition of Wide Bandgap Compound Semiconductors by Atom Probe Tomography: A Metrological Problem. *Microscopy and Microanalysis*, **2016**, 22, 650-651	0.5	1
471	Strain and compositional fluctuations in Al0.81In0.19N/GaN heterostructures. *Applied Physics Letters*, **2016**, 109, 132102	3.4	4
470	Backward diodes using heavily Mg-doped GaN growth by ammonia molecular-beam epitaxy. *Applied Physics Letters*, **2016**, 108, 072102	3.4	24
469	Exciton dynamics at a single dislocation in GaN probed by picosecond time-resolved cathodoluminescence. *Applied Physics Letters*, **2016**, 109, 042101	3.4	35
468	Statistical correction of atom probe tomography data of semiconductor alloys combined with optical spectroscopy: The case of Al0.25Ga0.75N. *Journal of Applied Physics*, **2016**, 119, 105704	2.5	42
467	Optical properties of nearly lattice-matched GaN/(Al,In)N quantum wells. *Journal of Applied Physics*, **2016**, 119, 205708	2.5	1
466	Vacancy-type defects in Mg-doped GaN grown by ammonia-based molecular beam epitaxy probed using a monoenergetic positron beam. *Journal of Applied Physics*, **2016**, 119, 245702	2.5	8
465	Low p-type contact resistance by field-emission tunneling in highly Mg-doped GaN. *Applied Physics Letters*, **2016**, 109, 252101	3.4	8
464	Calcium impurity as a source of non-radiative recombination in (In,Ga)N layers grown by molecular beam epitaxy. *Applied Physics Letters*, **2016**, 109, 212103	3.4	17
463	Quantification of roughness and spatial distribution of dislocations in MBE and MOVPE grown LED heterostructures. *Materials Science in Semiconductor Processing*, **2016**, 55, 12-18	4.3	3

462	InGaN laser diode with metal-free laser ridge using n+-GaN contact layers. *Applied Physics Express*, **2016**, 9, 061004	2.4	26
461	Continuous wave blue lasing in III-nitride nanobeam cavity on silicon. *Nano Letters*, **2015**, 15, 1259-63	11.5	44
460	Cavity-enhanced optical Hall effect in two-dimensional free charge carrier gases detected at terahertz frequencies. *Optics Letters*, **2015**, 40, 2688-91	3	12
459	Capacitance behavior of InAlN Schottky diodes in presence of large concentrations of shallow and deep states related to oxygen. *Journal of Applied Physics*, **2015**, 117, 185701	2.5	9
458	InGaN based micro light emitting diodes featuring a buried GaN tunnel junction. *Applied Physics Letters*, **2015**, 107, 051107	3.4	67
457	Phase and Spin Relaxation Dynamics in High-Quality Single GaN/AlGaN Quantum Well. *Springer Proceedings in Physics*, **2015**, 14-15	0.2	
456	Transport of dipolar excitons in (Al,Ga)N/GaN quantum wells. *Physical Review B*, **2015**, 91,	3.3	16
455	Vectorial near-field imaging of a GaN based photonic crystal cavity. *Applied Physics Letters*, **2015**, 107, 101110	3.4	4
454	GaN L3 Photonic Crystal Cavities With an Average Quality Factor in Excess of 16000 in the Near Infrared **2015**,		1
453	InGaN laser diodes emitting at 500 nm with p-layers grown by molecular beam epitaxy. *Applied Physics Express*, **2015**, 8, 022105	2.4	6
452	Solitary pulse-on-demand production by optical injection locking of passively Q-switched InGaN diode laser near lasing threshold. *Applied Physics Letters*, **2015**, 106, 071101	3.4	3
451	Self-aligned normally-off metal□xide□emiconductor n++GaN/InAlN/GaN high electron mobility transistors. *Physica Status Solidi (A) Applications and Materials Science*, **2015**, 212, 1086-1090	1.6	21
450	94-GHz Large-Signal Operation of AlInN/GaN High-Electron-Mobility Transistors on Silicon With Regrown Ohmic Contacts. *IEEE Electron Device Letters*, **2015**, 36, 17-19	4.4	37
449	Leakage mechanisms in InAlN based heterostructures. *Journal of Applied Physics*, **2014**, 115, 074506	2.5	26
448	M-Plane GaN/InAlN Multiple Quantum Wells in Core□Shell Wire Structure for UV Emission. *ACS Photonics*, **2014**, 1, 38-46	6.3	37
447	Biexcitonic molecules survive excitons at the Mott transition. *Nature Communications*, **2014**, 5, 5251	17.4	12
446	Composition of Wide Bandgap Semiconductor Materials and Nanostructures Measured by Atom Probe Tomography and Its Dependence on the Surface Electric Field. *Journal of Physical Chemistry C*, **2014**, 118, 24136-24151	3.8	114
445	Nano-scale luminescence characterization of individual InGaN/GaN quantum wells stacked in a microcavity using scanning transmission electron microscope cathodoluminescence. *Applied Physics Letters*, **2014**, 105, 032101	3.4	28

444	InGaN/GaN quantum wells for polariton laser diodes: Role of inhomogeneous broadening. *Journal of Applied Physics*, **2014**, 115, 233511	2.5	10
443	Hot-Electron-Related Degradation in InAlN/GaN High-Electron-Mobility Transistors. *IEEE Transactions on Electron Devices*, **2014**, 61, 2793-2801	2.9	33
442	Thermal stability and in situ SiN passivation of InAlN/GaN high electron mobility heterostructures. *Applied Physics Letters*, **2014**, 105, 112101	3.4	12
441	Low temperature p-type doping of (Al)GaN layers using ammonia molecular beam epitaxy for InGaN laser diodes. *Applied Physics Letters*, **2014**, 105, 241103	3.4	15
440	n+-GaN grown by ammonia molecular beam epitaxy: Application to regrown contacts. *Applied Physics Letters*, **2014**, 105, 202113	3.4	15
439	First demonstration of plasmonic GaN quantum cascade detectors with enhanced efficiency at normal incidence. *Optics Express*, **2014**, 22, 21069-78	3.3	11
438	Analysis of structurally sensitive loss in GaN-based VCSEL cavities and its effect on modal discrimination. *Optics Express*, **2014**, 22, 411-26	3.3	28
437	Interaction between meta-materials and shallow donors in bulk GaN at THz frequency. *Optics Express*, **2014**, 22, 3199-207	3.3	1
436	Shallow donor and deep DX-like center in InAlN layers nearly lattice-matched to GaN. *Physical Review B*, **2014**, 90,	3.3	11
435	High-temperature Mott transition in wide-band-gap semiconductor quantum wells. *Physical Review B*, **2014**, 90,	3.3	32
434	Triggering of guiding and antiguiding effects in GaN-based VCSELs **2014**,		1
433	Gallium nitride L3 photonic crystal cavities with an average quality factor of 16 900 in the near infrared. *Applied Physics Letters*, **2014**, 105, 231119	3.4	24
432	Ultrathin Body InAlN/GaN HEMTs for High-Temperature (600 $^{circ} {rm C}$) Electronics. *IEEE Electron Device Letters*, **2013**, 34, 496-498	4.4	21
431	Optical, structural, and morphological characterisation of epitaxial ZnO films grown by pulsed-laser deposition. *Thin Solid Films*, **2013**, 539, 55-59	2.2	21
430	AlInN-Based HEMTs for Large-Signal Operation at 40 GHz. *IEEE Transactions on Electron Devices*, **2013**, 60, 3091-3098	2.9	24
429	Impact of saturation on the polariton renormalization in III-nitride based planar microcavities. *Physical Review B*, **2013**, 88,	3.3	16
428	Engineering the Lateral Optical Guiding in Gallium Nitride-Based Vertical-Cavity Surface-Emitting Laser Cavities to Reach the Lowest Threshold Gain. *Japanese Journal of Applied Physics*, **2013**, 52, 08JG04	1.4	30
427	. *IEEE Photonics Technology Letters*, **2013**, 25, 1514-1516	2.2	6

426	Large-k exciton dynamics in GaN epilayers: Nonthermal and thermal regimes. *Physical Review B*, **2013**, 87,	3.3	9
425	Intrinsic degradation mechanism of nearly lattice-matched InAlN layers grown on GaN substrates. *Journal of Applied Physics*, **2013**, 113, 063506	2.5	49
424	Peculiarities in the pressure dependence of photoluminescence in InAlN. *Physica Status Solidi (B): Basic Research*, **2013**, 250, 677-682	1.3	3
423	. *IEEE Electron Device Letters*, **2013**, 34, 432-434	4.4	27
422	Q-factor of (In,Ga)N containing III-nitride microcavity grown by multiple deposition techniques. *Journal of Applied Physics*, **2013**, 114, 233102	2.5	10
421	ZrO2/InAlN/GaN Metal□Oxide□Semiconductor Heterostructure Field-Effect Transistors with InAlN Barrier of Different Compositions. *Japanese Journal of Applied Physics*, **2013**, 52, 08JN07	1.4	5
420	GaN-on-insulator technology for high-temperature electronics beyond 400 □C. *Semiconductor Science and Technology*, **2013**, 28, 074026	1.8	15
419	In-depth analysis of injection-seeded long external cavity InGaN/GaN surface-emitting laser. *Journal of Applied Physics*, **2013**, 113, 043108	2.5	2
418	AlN-Capped AlInN/GaN High Electron Mobility Transistors with 4.5 W/mm Output Power at 40 GHz. *Japanese Journal of Applied Physics*, **2013**, 52, 08JN16	1.4	5
417	Mode locking in monolithic two-section InGaN blue-violet semiconductor lasers. *Applied Physics Letters*, **2013**, 102, 121115	3.4	10
416	Ultrathin InAlN/GaN heterostructures on sapphire for high on/off current ratio high electron mobility transistors. *Journal of Applied Physics*, **2013**, 113, 214503	2.5	16
415	Integrated photonics on silicon with wide bandgap GaN semiconductor. *Applied Physics Letters*, **2013**, 102, 081120	3.4	47
414	Defect states characterization of non-annealed and annealed ZrO2/InAlN/GaN structures by capacitance measurements. *Applied Physics Letters*, **2013**, 102, 063502	3.4	8
413	Temperature-Dependence of Exciton Radiative Recombination in (Al,Ga)N/GaN Quantum Wells Grown ona-Plane GaN Substrates. *Japanese Journal of Applied Physics*, **2013**, 52, 08JC01	1.4	8
412	Growth of Thick GaN Layers by Hydride Vapor Phase Epitaxy on Sapphire Substrate with Internally Focused Laser Processing. *Applied Physics Express*, **2013**, 6, 035502	2.4	11
411	Properties of InAlN layers nearly lattice-matched to GaN and their use for photonics and electronics **2013**, 177-226		4
410	Toward Quantum Fluids at Room Temperature: Polariton Condensation in III-Nitride Based Microcavities. *Springer Series in Solid-state Sciences*, **2013**, 201-230	0.4	
409	Explanation of threshold voltage scaling in enhancement-mode InAlN/AlN□GaN metal oxide semiconductor high electron mobility transistors on Si substrates. *Thin Solid Films*, **2012**, 520, 6230-6232	2.2	16

408	Measurement of polarization-induced electric fields in GaN/AlInN quantum wells. *Applied Physics Letters*, **2012**, 101, 251902	3.4	8
407	Early stage degradation of InAlN/GaN HEMTs during electrical stress **2012**,		1
406	High quality factor two dimensional GaN photonic crystal cavity membranes grown on silicon substrate. *Applied Physics Letters*, **2012**, 100, 071103	3.4	50
405	InAlN/GaN HEMTs for Operation in the 1000 $^{circ} hbox{C}$ Regime: A First Experiment. *IEEE Electron Device Letters*, **2012**, 33, 985-987	4.4	58
404	Generic picture of the emission properties of III-nitride polariton laser diodes: Steady state and current modulation response. *Physical Review B*, **2012**, 86,	3.3	19
403	Thermal annealing of molecular beam epitaxy-grown InGaN/GaN single quantum well. *Semiconductor Science and Technology*, **2012**, 27, 105023	1.8	9
402	Thermal carrier emission and nonradiative recombinations in nonpolar (Al,Ga)N/GaN quantum wells grown on bulk GaN. *Journal of Applied Physics*, **2012**, 111, 033517	2.5	10
401	Mg doping for p-type AlInN lattice-matched to GaN. *Applied Physics Letters*, **2012**, 101, 082113	3.4	36
400	Blue monolithic AlInN-based vertical cavity surface emitting laser diode on free-standing GaN substrate. *Applied Physics Letters*, **2012**, 101, 151113	3.4	109
399	A simplified GaN/AlGaN quantum cascade detector with an alloy extractor. *Applied Physics Letters*, **2012**, 101, 251101	3.4	19
398	Two-color GaN/AlGaN quantum cascade detector at short infrared wavelengths of 1 and 1.7 Ìm. *Applied Physics Letters*, **2012**, 100, 181103	3.4	43
397	Low loss EEL spectroscopy performed on InxAl1-xN layers grown by MOVPE: comparison between experiment and ab-initio calculations. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 989-992		2
396	Investigation of InGaN/GaN quantum wells for polariton laser diodes. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 1325-1329		6
395	GaN on sapphire mesa technology. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2012**, 9, 945-948		5
394	Superluminescent light emitting diodes: the best out of two worlds **2012**,		16
393	Near-infrared characterization of gallium nitride photonic-crystal waveguides and cavities. *Optics Letters*, **2012**, 37, 4588-90	3	23
392	Optically pumped long external cavity InGaN/GaN surface-emitting laser with injection seeding from a planar microcavity. *Applied Physics Letters*, **2012**, 101, 141120	3.4	8
391	Nonlinear emission properties of an optically anisotropic GaN-based microcavity. *Physical Review B*, **2012**, 86,	3.3	5

390	On the origin of basal stacking faults in nonpolar wurtzite films epitaxially grown on sapphire substrates. *Journal of Applied Physics*, **2012**, 112, 113518	2.5	20
389	Impact of biexcitons on the relaxation mechanisms of polaritons in III-nitride based multiple quantum well microcavities. *Physical Review B*, **2012**, 85,	3.3	13
388	Buffer-Related Degradation Aspects of Single and Double-Heterostructure Quantum Well InAlN/GaN High-Electron-Mobility Transistors. *Japanese Journal of Applied Physics*, **2012**, 51, 054102	1.4	2
387	Static and dynamic properties of multi-section InGaN-based laser diodes. *Journal of Applied Physics*, **2012**, 112, 103112	2.5	10
386	Buffer-Related Degradation Aspects of Single and Double-Heterostructure Quantum Well InAlN/GaN High-Electron-Mobility Transistors. *Japanese Journal of Applied Physics*, **2012**, 51, 054102	1.4	13
385	Advantages and remaining issues of state-of-the-artm-plane freestanding GaN substrates grown by halide vapor phase epitaxy form-plane InGaN epitaxial growth. *Semiconductor Science and Technology*, **2012**, 27, 024008	1.8	15
384	One-dimensional exciton luminescence induced by extended defects in nonpolar GaN/(Al,Ga)N quantum wells. *Semiconductor Science and Technology*, **2011**, 26, 025012	1.8	15
383	Recombination coefficients of GaN-based laser diodes. *Journal of Applied Physics*, **2011**, 109, 093106	2.5	72
382	. *IEEE Electron Device Letters*, **2011**, 32, 1364-1366	4.4	60
381	Diamond overgrown InAlN/GaN HEMT. *Diamond and Related Materials*, **2011**, 20, 604-608	3.5	45
380	Effects of the annealing temperature on the structural and electronic properties of MBE grown InGaN/GaN quantum wells. *Journal of Physics: Conference Series*, **2011**, 326, 012012	0.3	
379	TEM and XANES study of MOVPE grown InAlN layers with different indium content. *Journal of Physics: Conference Series*, **2011**, 326, 012013	0.3	8
378	Standard-free composition measurements of Alx In1⊠N by low-loss electron energy loss spectroscopy. *Physica Status Solidi - Rapid Research Letters*, **2011**, 5, 50-52	2.5	14
377	High-speed and low-noise AlInN/GaN HEMTs on SiC. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 429-433	1.6	7
376	Investigation of the In composition in InGaN/GaN quantum wells deposited by MOVPE and/or MBE with emission from violet to green. *Physica Status Solidi (B): Basic Research*, **2011**, 248, 1187-1190	1.3	12
375	Measurement of the tuneable absorption in GaN-based multi-section laser diodes. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2345-2347		2
374	Time-resolved cathodoluminescence on polychromatic light emitting (In,Ga)N quantum wells grown on (11-22) GaN facets. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 1394-1397		5
373	A novel class of coherent light emitters: polariton lasers. *Semiconductor Science and Technology*, **2011**, 26, 014030	1.8	22

372	Electrical properties of InAlN/GaN high electron mobility transistor with Al2O3, ZrO2, and GdScO3 gate dielectrics. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2011**, 29, 01A808	1.3	26
371	Self heating in AlInN/AlN/GaN high power devices: Origin and impact on contact breakdown and IV characteristics. *Journal of Applied Physics*, **2011**, 109, 063720	2.5	21
370	Defects in a-GaN grown on r-sapphire by hydride vapor phase epitaxy. *Journal of Crystal Growth*, **2011**, 327, 6-12	1.6	5
369	Implementation of Spatio-Time-Resolved Cathodoluminescence Spectroscopy for Studying Local Carrier Dynamics in a Low Dislocation Density m-Plane In$_{0.05}$Ga$_{0.95}$N Epilayer Grown on a Freestanding GaN Substrate. *Japanese Journal of Applied Physics*, **2011**, 50, 111002	1.4	6
368	Tailoring the light-matter coupling in anisotropic microcavities: Redistribution of oscillator strength in strained m-plane GaN/AlGaN quantum wells. *Physical Review B*, **2011**, 84,	3.3	13
367	Stress-modulated composition in the vicinity of dislocations in nearly lattice matched AlxIn1−xN/GaN heterostructures: A possible explanation of defect insensitivity. *Physical Review B*, **2011**, 83,	3.3	22
366	Polariton lasing in a hybrid bulk ZnO microcavity. *Applied Physics Letters*, **2011**, 99, 161104	3.4	81
365	Optical bistability in InGaN-based multisection laser diodes. *Applied Physics Letters*, **2011**, 98, 191115	3.4	8
364	Intrinsic dynamics of weakly and strongly confined excitons in nonpolar nitride-based heterostructures. *Physical Review B*, **2011**, 83,	3.3	26
363	Role of stable and metastable Mg–H complexes in p-type GaN for cw blue laser diodes. *Applied Physics Letters*, **2011**, 98, 213505	3.4	55
362	Si-interdiffusion in heavily doped AlN-GaN-based quantum well intersubband photodetectors. *Applied Physics Letters*, **2011**, 98, 241101	3.4	4
361	Strain compensation in AlInN/GaN multilayers on GaN substrates: Application to the realization of defect-free Bragg reflectors. *Applied Physics Letters*, **2011**, 98, 181111	3.4	51
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